SS34-320

Schottky Barrier Diode

Features

- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters,
- free wheeling, and polarity protection applications
- Metal silicon junction, majority carrier conduction
- Approx. Weight : 60mg

Pb Free

ROHS Compliant

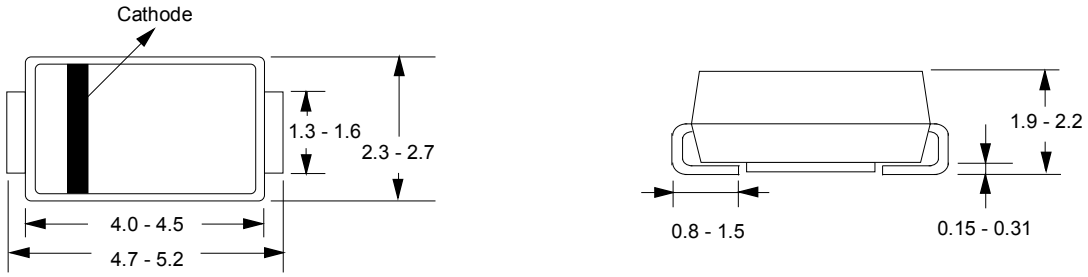
Green Product

Making :

SS34	SS34
SS36	SS36
SS310	SS310
SS320	SS320

PACKAGE DIMENSIONS in millimeters (mm):

SMA



Packing : 2000pcs/reel

Maximum Ratings And Electrical Characteristics (Ta=25°C unless otherwise noted)

Parameter	Symbols	SS34	SS36	SS310	SS320	Units
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	40	60	100	200	V
Maximum RMS voltage	V_{RMS}	28	42	70	140	V
Maximum DC Blocking Voltage	V_{DC}	40	60	100	200	V
Maximum Average Forward Rectified Current	$I_{F(AV)}$	3.0				A
Peak Forward Surge Current,8.3ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	80				A
Max Instantaneous Forward Voltage at 3A	V_F	0.55	0.70	0.85	0.95	V
Maximum DC Reverse Current T_a = 25°C At Rated DC Reverse Voltage T_a =100°C	I_R	0.5 5	0.3 3			mA
Typical Junction Capacitance (1)	C_j	450	400			pF
Typical Thermal Resistance (2)	$R_{\theta JA}$	70				°C/W
Operating Junction Temperature Range	T_j	-55 ~ +125				°C
Storage Temperature Range	T_{stg}	-55 ~ +150				°C

(1)Measured at 1 MHz and applied reverse voltage of 4 V D.C

(2)P.C.B. mounted with 2.0" X 2.0" (5 X 5 cm) copper pad areas.

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Typical Characteristics

Fig.1 Forward Current Derating Curve

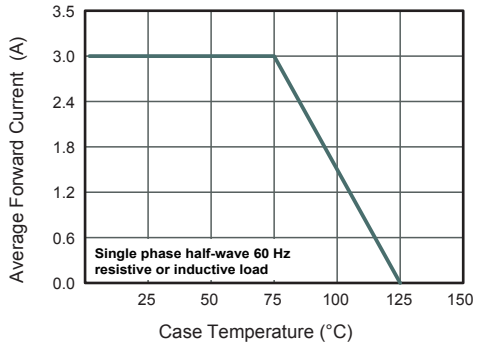

Fig.2 Typical Reverse Characteristics

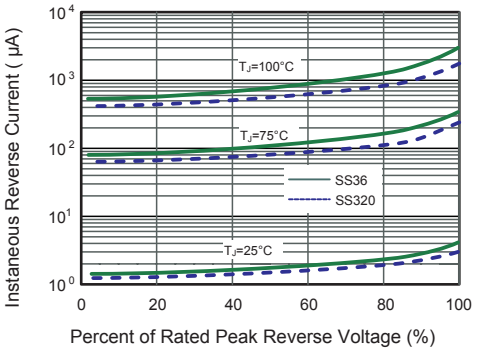

Fig.3 Typical Forward Characteristic

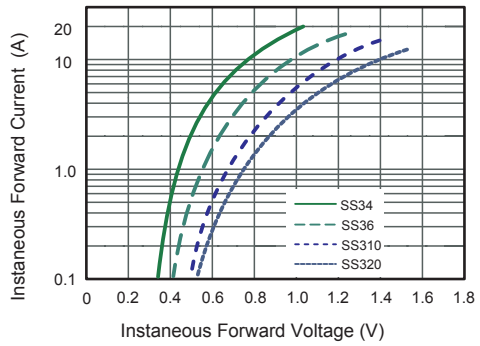

Fig.4 Typical Junction Capacitance

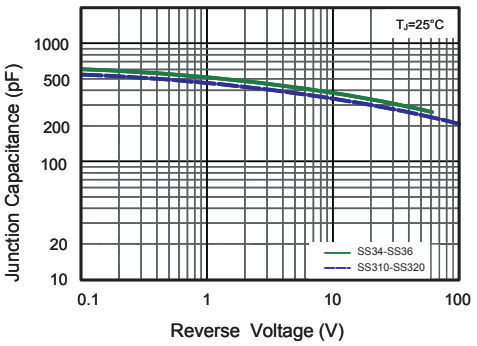

Fig.5 Maximum Non-Repetitive Peak Forward Surage Current

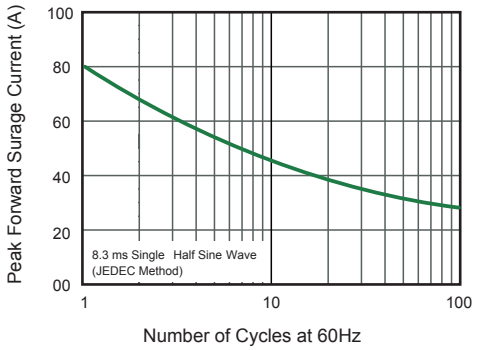

Fig.5- Typical Transient Thermal Impedance